

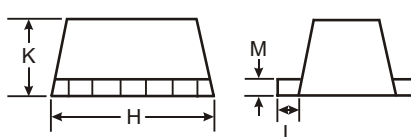
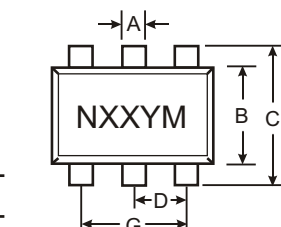
NPN PRE-BIASED SMALL SIGNAL SOT-563 DUAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDA)
- Built-In Biasing Resistors
- Lead-Free Device

Mechanical Data

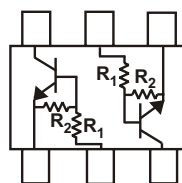
- Case: SOT-563, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208 (Note 2)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (approx.)



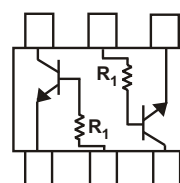
SEE NOTE 1

SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.15	0.25	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

P/N	R1	R2	MARKING
DDC124EH	22K Ω	22K Ω	N17
DDC144EH	47K Ω	47K Ω	N20
DDC143EH	4.7K Ω	4.7K Ω	N08
DDC114YH	10K Ω	47K Ω	N14
DDC123JH	2.2K Ω	47K Ω	N06
DDC114EH	10K Ω	10K Ω	N13
DDC143TH	4.7K Ω	-	N07
DDC114TH	10K Ω	-	N12



R₁, R₂



R₁ Only

SCHEMATIC DIAGRAM, TOP VIEW

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10 to +40 -10 to +40 -10 to +30 -6 to +40 -5 to +12 -10 to +40 -5 V _{max} -5 V _{max}	V
Output Current	I _O	30 30 100 70 100 50 100 100	mA
Output Current All	I _C (Max)	100	mA
Power Dissipation	P _d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 3)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Note:
1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
 2. If lead-bearing terminal plating is required, please contact your Diodes Inc. sales representative for availability and minimum order details.
 3. Mounted on FR4 Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic (DDC143TH & DDC114TH only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 50\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 50\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50\text{V}$
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_B = 2.5\text{mA} / 0.25\text{mA}$ DDC143TH $I_C/I_B = 1\text{mA} / 0.1\text{mA}$ DDC114TH
DC Current Transfer Ratio	h_{FE}	100	250	600	—	$I_C = 1\text{mA}$, $V_{CE} = 5\text{V}$
Gain-Bandwidth Product*	f_T	—	250	—	MHz	$V_{CE} = 10\text{V}$, $I_E = -5\text{mA}$, $f = 100\text{MHz}$

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	$V_{I(off)}$	0.5 0.5 0.5 0.3 0.5 0.5	1.1 1.1 1.1 — — 1.1	—	V	$V_{CC} = 5\text{V}$, $I_O = 100\mu\text{A}$
	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	$V_{I(on)}$	—	1.9 1.9 1.9 — — 1.9	3.0 3.0 3.0 1.4 1.1 3.0		$V_O = 0.3\text{V}$, $I_O = 5\text{mA}$ $V_O = 0.3\text{V}$, $I_O = 2\text{mA}$ $V_O = 0.3\text{V}$, $I_O = 20\text{mA}$ $V_O = 0.3\text{V}$, $I_O = 1\text{mA}$ $V_O = 0.3\text{V}$, $I_O = 5\text{mA}$ $V_O = 0.3\text{V}$, $I_O = 10\text{mA}$
Output Voltage	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	$V_{O(on)}$	—	0.1	0.3	V	$I_O/I_I = 10\text{mA} / 0.5\text{mA}$ $I_O/I_I = 10\text{mA} / 0.5\text{mA}$ $I_O/I_I = 10\text{mA} / 0.5\text{mA}$ $I_O/I_I = 5\text{mA} / 0.25\text{mA}$ $I_O/I_I = 5\text{mA} / 0.25\text{mA}$ $I_O/I_I = 10\text{mA} / 0.5\text{mA}$
Input Current	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	I_I	—	—	0.36 0.18 1.8 0.88 3.6 0.88	mA	$V_I = 5\text{V}$
Output Current		$I_{O(off)}$	—	—	0.5	μA	$V_{CC} = 50\text{V}$, $V_I = 0\text{V}$
DC Current Gain	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	G_I	56 68 20 68 80 30	—	—	—	$V_O = 5\text{V}$, $I_O = 5\text{mA}$ $V_O = 5\text{V}$, $I_O = 5\text{mA}$ $V_O = 5\text{V}$, $I_O = 10\text{mA}$ $V_O = 5\text{V}$, $I_O = 10\text{mA}$ $V_O = 5\text{V}$, $I_O = 10\text{mA}$ $V_O = 5\text{V}$, $I_O = 5\text{mA}$
Gain-Bandwidth Product*		f_T	—	250	—	MHz	$V_{CE} = 10\text{V}$, $I_E = 5\text{mA}$, $f = 100\text{MHz}$

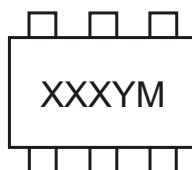
* Transistor - For Reference Only

Ordering Information (Note 4)

Device	Packaging	Shipping
DDC124EH-7	SOT-563	3000/Tape & Reel
DDC144EH-7	SOT-563	3000/Tape & Reel
DDC143EH-7	SOT-563	3000/Tape & Reel
DDC114YH-7	SOT-563	3000/Tape & Reel
DDC123JH-7	SOT-563	3000/Tape & Reel
DDC114EH-7	SOT-563	3000/Tape & Reel
DDC143TH-7	SOT-563	3000/Tape & Reel
DDC114TH-7	SOT-563	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



XXX = Product Type Marking Code (See Page 1)

YM = Date Code Marking

Y = Year ex: P = 2003

M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

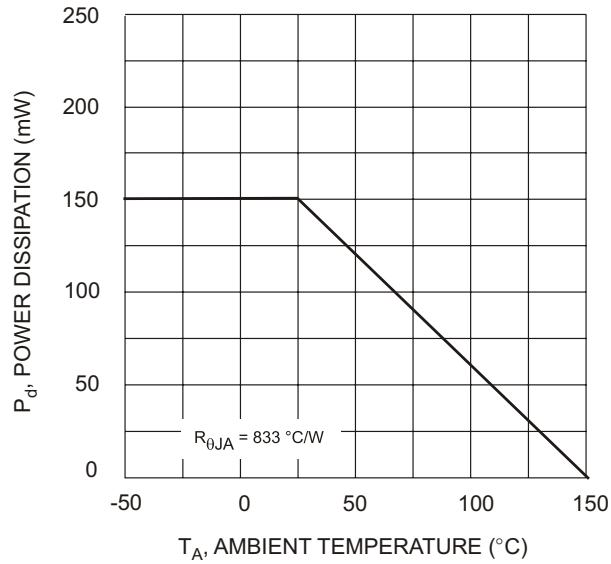
TYPICAL CURVES - DDC143EH
NEW PRODUCT


Fig. 1 Derating Curve

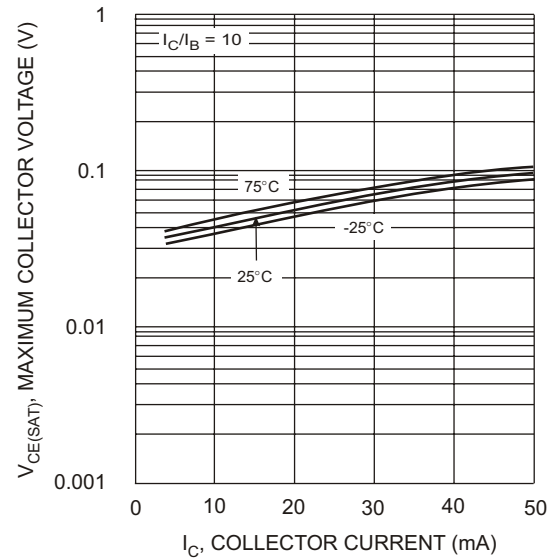
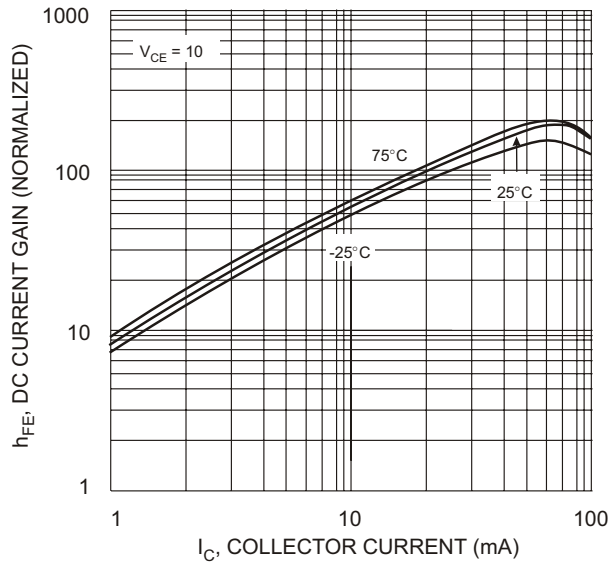

 Fig. 2 $V_{CE(SAT)}$ vs. I_C


Fig. 3 DC Current Gain

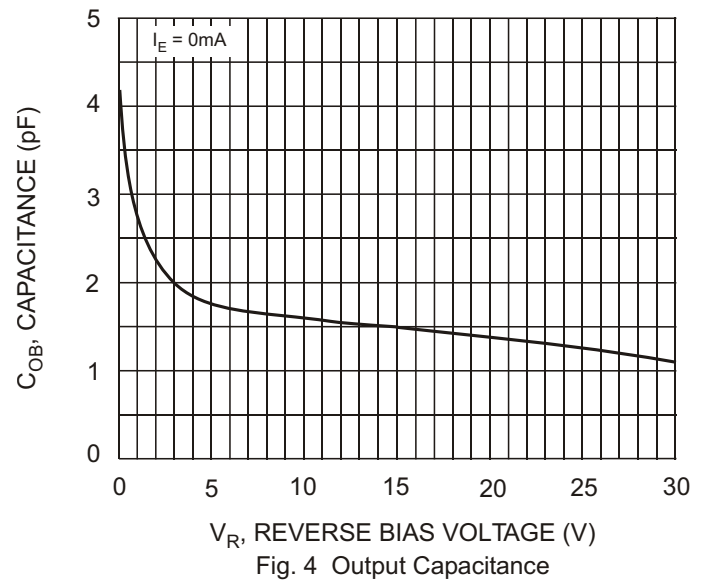


Fig. 4 Output Capacitance

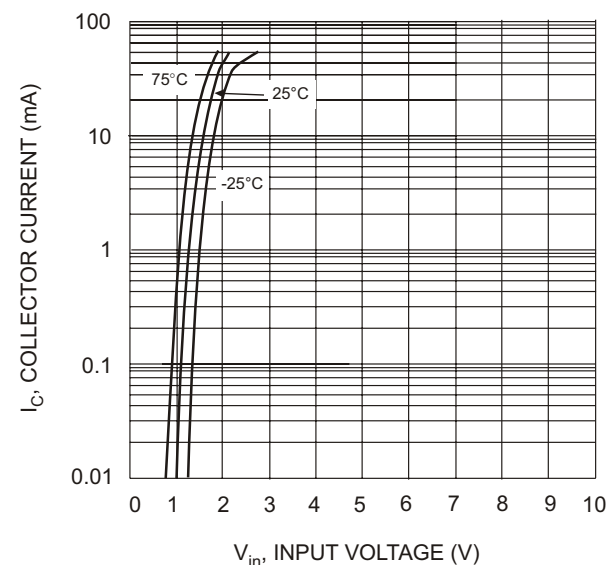


Fig. 5 Collector Current Vs. Input Voltage

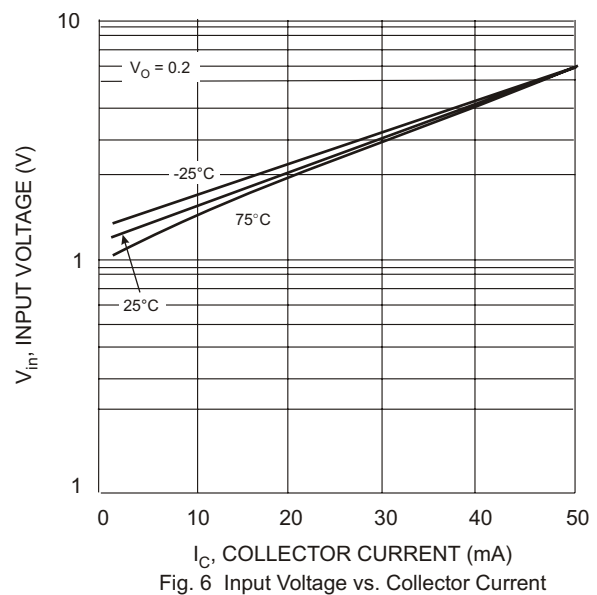


Fig. 6 Input Voltage vs. Collector Current